

Cont'd
B1
H₂ to said insulating layer, said silicon-containing structure and said conductive structure, such that the reaction between said O₂ and H₂ does not increase the pressure in the processing chamber beyond a predetermined level.

B2
B2 sub 2
9 (Twice Amended). A method of oxidizing, in a semiconductor processing chamber, a first feature while leaving a second feature substantially unoxidized, said method comprised of subjecting said first and second features to O₂ and H₂, such that the reaction between said O₂ and H₂ does not increase the pressure in the processing chamber beyond a predetermined level.

B3
B3 sub 3
16 (Twice Amended). A method of fabricating, in a semiconductor processing chamber, a capacitor having a dielectric between a bottom electrode and a top electrode and situated over a semiconductor substrate, said method comprising the steps of:
providing said bottom electrode over said semiconductor substrate;
providing a dielectric material over said bottom electrode; and
subjecting said bottom electrode and said dielectric material to O₂ and H₂, wherein said dielectric material is oxidized and said bottom electrode remains substantially unoxidized, such that the reaction between said O₂ and H₂ does not increase the pressure in the processing chamber beyond a predetermined level.

B4
B4 sub 4
20 (Amended). The method of claim 1 wherein said oxidizing step comprises the step of oxidizing a portion of said insulating layer and said silicon-containing structure while leaving said conductive structure substantially unoxidized by introducing O₂ and H₂ in a portion of a process chamber's total volume, such that reaction between the O₂ and H₂ occurs continuously as the O₂ and H₂ enter the chamber.

B5
B5 sub 5
22 (Amended). The method of claim 9 and further comprising the step of introducing O₂ and H₂ in a portion of a process chamber's total volume, such that

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reaction between the O₂ and H₂ occurs continuously as the O₂ and H₂ enter the chamber.

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24 (Amended). The method of claim 16 and further comprising the step of introducing O₂ and H₂ in a portion of a process chamber's total volume, such that reaction between the O₂ and H₂ occurs continuously as the O₂ and H₂ enter the chamber.

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B7
26 (Amended). A method of fabricating an electrical device formed in a semiconductor substrate, said method comprising:
forming an insulating layer over said semiconductor substrate;
forming a silicon-containing structure on said insulating layer;
forming a conductive structure on said silicon-containing structure; and
oxidizing a portion of said insulating layer and said silicon-containing structure while leaving said conductive structure substantially unoxidized by introducing an oxygen-containing gas selected from the group consisting of O₂, N₂O, CO₂ and a separate hydrogen-containing gas to said insulating layer, said silicon-containing structure and said conductive structure, such that the reaction between said O₂ and H₂ does not increase the pressure in the processing chamber beyond a predetermined level.

27 (Amended). The method of claim 26 wherein said oxidizing step comprises the step of oxidizing a portion of said insulating layer and said silicon-containing structure while leaving said conductive structure substantially unoxidized by introducing said oxygen-containing gas and said hydrogen containing gas in a portion of a process chamber's total volume, such that reaction between the O₂ and H₂ occurs continuously as the O₂ and H₂ enter the chamber.

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29 (New). The method of claim 1 wherein said oxidizing step comprises the step of oxidizing a portion of said insulating layer and said silicon-containing structure while leaving said conductive structure substantially unoxidized by introducing O₂ and